

IN THE SPECIFICATION

Please replace the paragraph beginning at page 9, line 25, with the following rewritten paragraph:

B1
Next, the interlayer insulating film 213 is etched by dry etching, using the resist film 216 as a mask, as shown in FIG. 4A. At this time, the silicon nitride film 215 and the silicon nitride film of the cap material 211 are etched in correspondence with the etching selection ratio between the interlayer insulating film 213 and the silicon nitride film. Generally, etching is concentrated on end parts of the gate, so that the film is reduced more. Therefore, a silicon dioxide film 214 is exposed at a part. Thereafter, interfacial cleaning is performed on the structure shown in FIG. 4A. In the worst case, the silicon dioxide film 214 can be etched back.

Please replace the paragraph beginning at page 10, line 10, with the following rewritten paragraph:

B2
~~Thereafter, interfacial cleaning is performed on the structure shown in FIG. 4A.~~
Thereafter, a contact material 217, e.g., metal such as a low-resistance polysilicon or tungsten (W) is buried. Further, as shown in FIG. 4B, the contact material 217 is flattened to finish a contact.